CNA1012K (ON1114)

Photo Interrupter

For contactless SW and object detection

Overview

CNA1012K is a photocoupler in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

Features

- Highly precise position detection: 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response: t_r , $t_f = 6 \ \mu s$ (typ.)
- Small output current variation against change in temperature
- Large output current

Absolute Maximum Ratings $T_a = 25\Sigma\Delta\gamma\rho C$

F	Symbol	Rating	Unit		
Input (Light emitting diode)	Power dissipation *1	PD	75	mW	
	Forward current	I _F	50	mA	
	Reverse voltage V _R 3		V		
Output (Photo transistor)	Collector-emitter voltage V _{CEO} 30		30	v	
	Emitter-collector voltage (Base open)	V _{ECO}	5005	V X	
	Collector current	Ic	20	mA	
	Collector power dissipation *2	P _C	100	mW	
Operating ambient temp	T _{opr}	-25 to +85	°C		
Storage temperature	T _{stg}	-30 to +100	°C		

Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C.

*2: Output power derating ratio is 1.34 mW/°C at $T_a \ge 25$ °C.

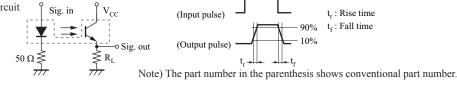
Electrical-Optical Characteristics $T_a = 25\Sigma\Delta\gamma\rho C \pm 3\Sigma\Delta\gamma\rho C$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I _R	$V_R = 3V$			10	μΑ
	Forward voltage	V _F	$I_{\rm F} = 50 {\rm mA}$		1.2	1.5	V
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 V$			200	nA
	Collector-emitter capacitance	C _C	$V_{CE} = 10 \text{ V}, \text{ f} = 1 \text{ MHz}$		5		pF
Transfer characteristics	Collector current	I _C	$V_{CE} = 10 \text{ V}, I_F = 20 \text{ mA}$	0.7			mA
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 50 \text{ mA}, I_C = 0.1 \text{ mA}$			0.3	V
	Rise time *	t _r	$V_{\rm CC} = 10 \text{ V}, I_{\rm C} = 1 \text{ mA},$		6.0		μs
	Fall time *	t _f	$R_L = 100 \Omega$		6.0		μs

Note) 1. Input and output are practiced by electricity.

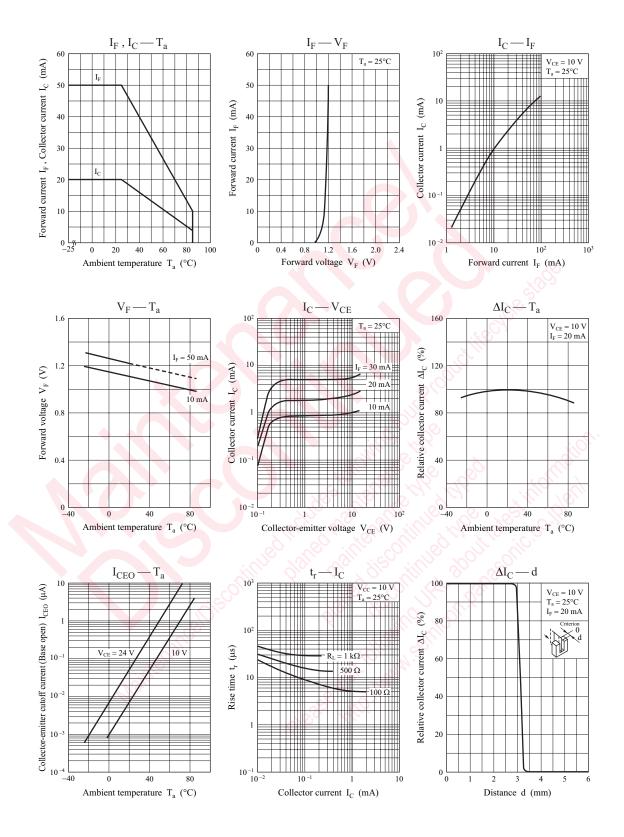
2. This device is designed by disregarding radiation.

3. *: Switching time measurement circuit ^o Si



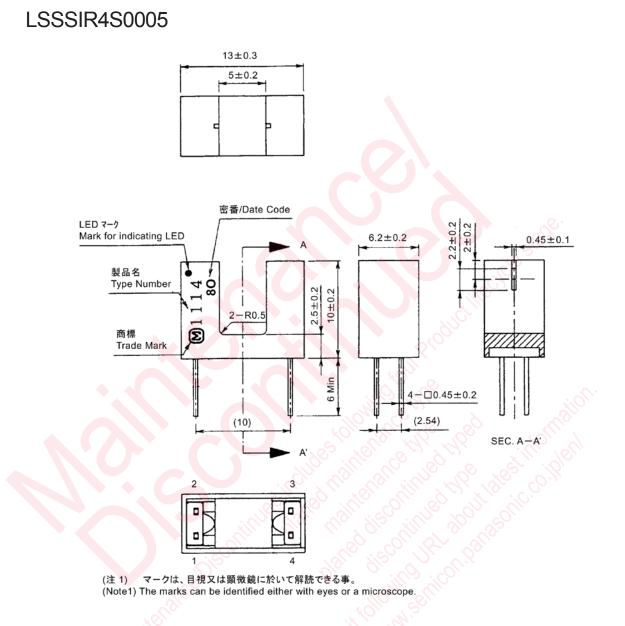
CNA1012K

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Package (Unit: mm)



- Pin name
 - 1: Anode
 - 2: Cathode
 - 3: Collector
 - 4: Emitter

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